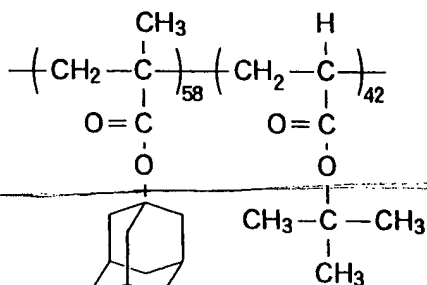


## AMENDMENT TO THE ABSTRACT:

Please amend the Abstract as follows:

~~A copolymer expressed by the following structural formula~~



~~was obtained by loading adamantly methacrylate monomer and t butyl acrylate monomer by 1:1, then conducting polymerization, adding AIBN as a polymerization initiator, and then conducting precipitation purification with methanol. Then to the copolymer, triphenylsulfonium hexafluoroantimonate was added to prepare a cyclohexanone solution. This solution was applied to a wafer, and exposed to a KrF excimer stepper and developed. The threshold energy Eth was 50 mJ/cm<sup>2</sup>. A 0.45 μm-wide L & S was formed at 130 mJ/cm<sup>2</sup>. The radiation sensitive material has good transparency and etching resistance, high sensitivity, and little peeling.~~

A radiation sensitive material comprising a copolymer including itaconic anhydride and methods of using such radiation sensitive materials in methods for forming a pattern.